Standard NAND Flash Part Numbering System
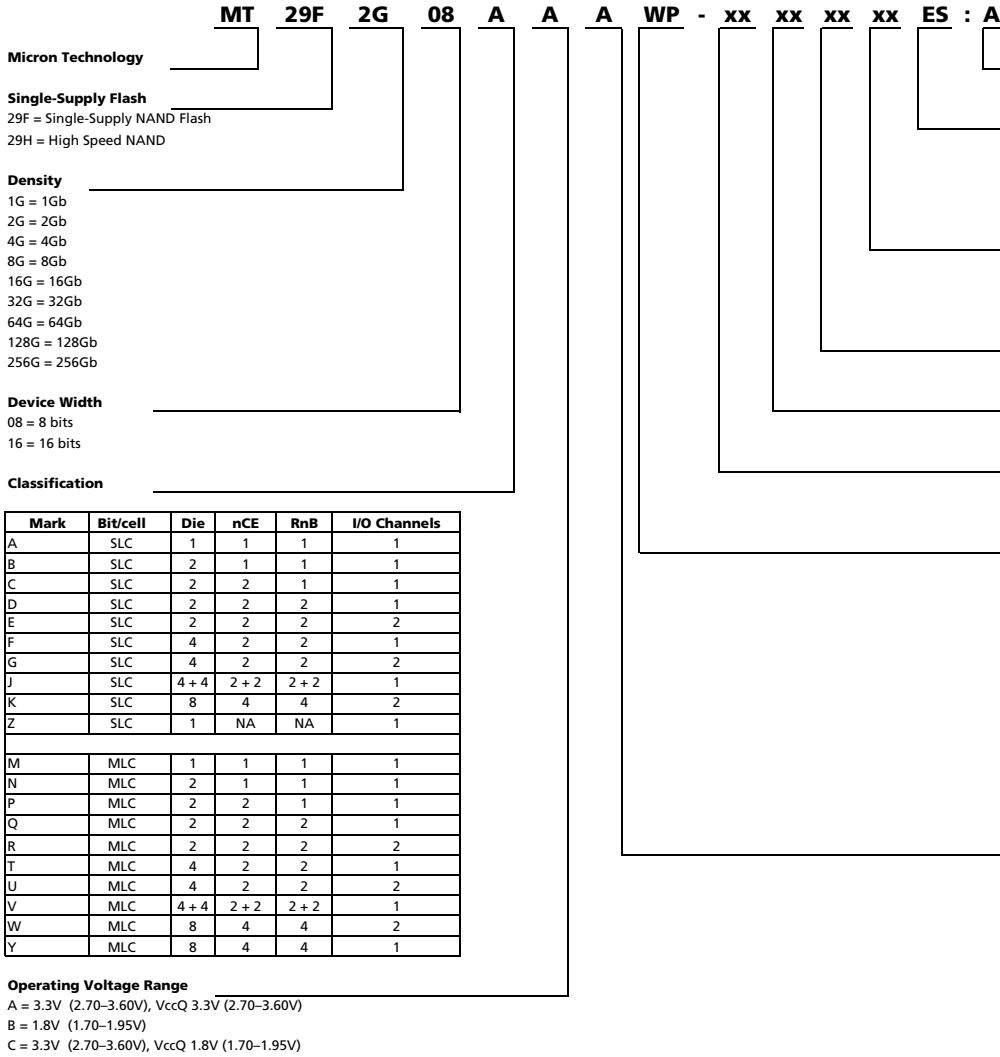
Micron's part numbering system is available at **www.micron.com/support/designsupport/documents/png**

Standard NAND Flash*

MT 29F 2G 08 A A A WP - xx xx xx xx ES : A

Micron Technology

Single-Supply Flash
29F = Single-Supply NAND Flash
29H = High Speed NAND

Density
1G = 1Gb
2G = 2Gb
4G = 4Gb
8G = 8Gb
16G = 16Gb
32G = 32Gb
64G = 64Gb
128G = 128Gb
256G = 256Gb

Device Width
08 = 8 bits
16 = 16 bits

Classification

Mark	Bit/cell	Die	nCE	RnB	I/O Channels
A	SLC	1	1	1	1
B	SLC	2	1	1	1
C	SLC	2	2	1	1
D	SLC	2	2	2	1
E	SLC	2	2	2	2
F	SLC	4	2	2	1
G	SLC	4	2	2	2
J	SLC	4 + 4	2 + 2	2 + 2	1
K	SLC	8	4	4	2
Z	SLC	1	NA	NA	1
M	MLC	1	1	1	1
N	MLC	2	1	1	1
P	MLC	2	2	1	1
Q	MLC	2	2	2	1
R	MLC	2	2	2	2
T	MLC	4	2	2	1
U	MLC	4	2	2	2
V	MLC	4 + 4	2 + 2	2 + 2	1
W	MLC	8	4	4	2
Y	MLC	8	4	4	1

Operating Voltage Range
A = 3.3V (2.70–3.60V), VccQ 3.3V (2.70–3.60V)
B = 1.8V (1.70–1.95V)
C = 3.3V (2.70–3.60V), VccQ 1.8V (1.70–1.95V)

Design Revision (shrink)
A = 1st design revision

Production Status
Blank = Production
ES = Engineering samples
QS = Qualification samples
MS = Mechanical samples

Operating Temperature Range
Blank = Commercial (0°C to +70°C)
ET = Extended (–40°C to +85°C)
WT = Wireless (–25°C to +85°C)

Block Option (Reserved for use)
Blank = Standard device

Flash Performance
Blank = Full specification

Speed Grade (MT29H Only)
15 = 133 MT/s
12 = 166 MT/s

Package Code
WP = 48-pin TSOP I (CPL version) (Pb-free)
WC = 48-pin TSOP I (OCPL version) (Pb-free)
H1 = 100-ball VFBGA (Pb-free), 12 x 18 x 1.0
H2 = 100-ball TFBGA (Pb-free), 12 x 18 x 1.2
HC = 63-ball VFBGA, 10.5 x 13 x 1.0
C2 = 52-pad ULGA, 12 x 17 x 0.4 (use TBD)
C3 = 52-pad ULGA, 12 x 17 x 0.65
C4 = 52-pad VLGA, 12 x 17 x 1.0 (SDP/DDP/QDP)
C5 = 52-pad VLGA, 14 x 18 x 1.0 (SDP/DDP/QDP)
C6 = 52-pad LLGA, 14 x 18 x 1.47 (8DP, QDP, DDP)
C7 = 48-pad LLGA, 12 x 20 x 1.47 (8DP)
SWC = 48-pin Stacked TSOP (OCPL version) (Pb-free)
SWP = 48-pin Stacked TSOP (CPL version) (Pb-free)

Generation (M29 only)/Feature Set
A = 1st set of device features
B = 2nd set of device features (rev only if different than 1st set)
C = 3rd set of device features (rev only if different)
D = 4th set of device features (rev only if different)
etc.

*Contact Micron for help differentiating between standard and next-generation NAND offerings.